Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (DTMOS II)

TK20D60U

Switching Regulator Applications

• Low drain-source ON-resistance: RDS (ON) = 0.165Ω (typ.)

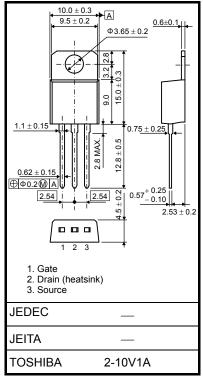
• High forward transfer admittance: $|Y_{fs}| = 12 \text{ S (typ.)}$

• Low leakage current: $I_{DSS} = 100 \mu A (V_{DS} = 600 \text{ V})$

• Enhancement mode: $V_{th} = 3.0 \text{ to } 5.0 \text{ V (VDS} = 10 \text{ V, ID} = 1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Gate-source voltage		V_{GSS}	±30	V	
Drain current	DC (Note 1)	I _D	20		
	Pulse (t = 1 ms) (Note 1)	I _{DP}	40	А	
Drain power dissipati	on (Tc = 25°C)	PD	190	W	
Single pulse avalanche energy (Note 2)		E _{AS}	144	mJ	
Avalanche current (Note 3)		I _{AR}	20	Α	
Repetitive avalanche energy		E _{AR}	19	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 1.35 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

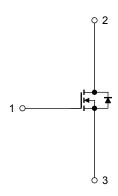
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R _{th (ch-c)}	0.658	°C/W	
Thermal resistance, channel to ambient	R _{th (ch-a)}	83.3	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 0.63 mH, R_G = 25 Ω , I_{AR} = 20 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.





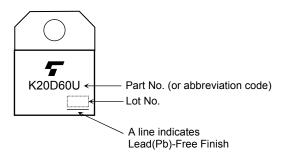
Electrical Characteristics (Ta = 25°C)

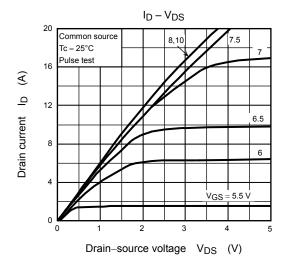
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current		I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source brea	akdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_		V
Gate threshold vo	oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	3.0	_	5.0	V
Drain-source ON	-resistance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 10 A	_	0.165	0.19	Ω
Forward transfer	admittance	Y _{fs}	V _{DS} = 10 V, I _D = 10 A	3.0	12		S
Input capacitance		C _{iss}		_	1470		
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	150		pF
Output capacitance		C _{oss}			3500		
Switching time	Rise time	t _r	$\begin{array}{c c} 10 \text{ V} & \text{I}_{D} = 10 \text{ A} & \text{V}_{OUT} \\ \hline \text{VGS} & \text{O} & \text{V} & \text{RL} = \\ \hline 50 \Omega & \text{W} & \text{NDD} \approx 300 \text{ V} \\ \end{array}$	_	40	_	. ns
	Turn-on time	t _{on}			80		
	Fall time	t _f			12		
	Turn-off time	t _{off}	Duty ≤ 1%, t _W = 10 μs	_	100	_	
Total gate charge		Qg		_	27	_	
Gate-source charge		Q _{gs}	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	_	16	_	nC
Gate-drain charge		Q _{gd}		_	11		

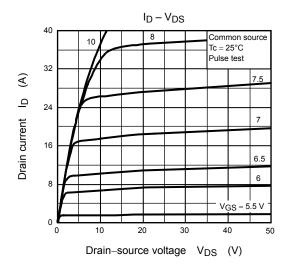
Source-Drain Ratings and Characteristics (Ta = 25°C)

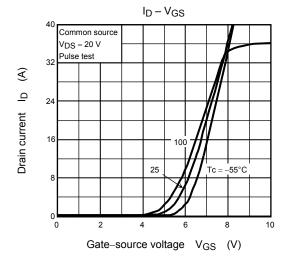
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	20	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	40	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 20 \text{ A}, V_{GS} = 0 \text{ V},$	_	450	_	ns
Reverse recovery charge	Q _{rr}	dl _{DR} /dt = 100 A/μs	_	8.1	_	μС

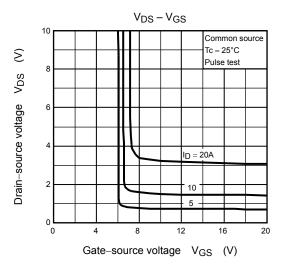
Marking

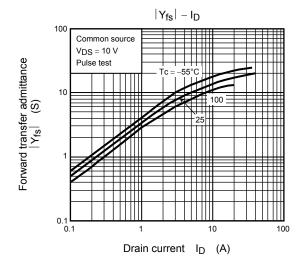


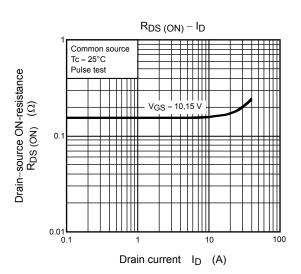


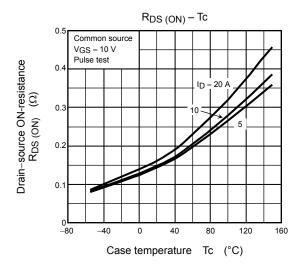


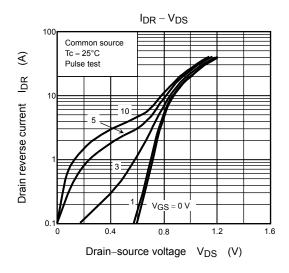


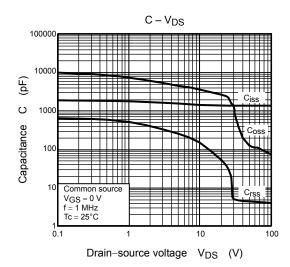


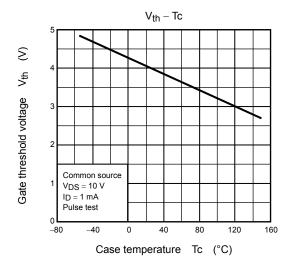


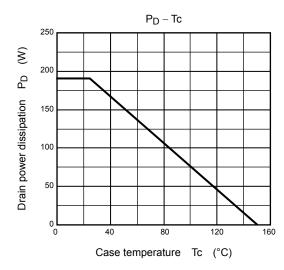


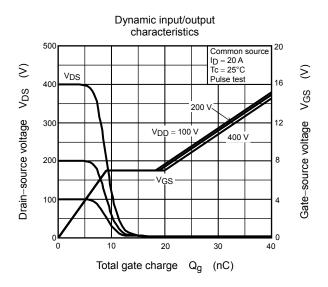


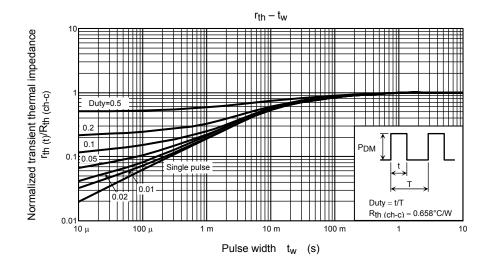


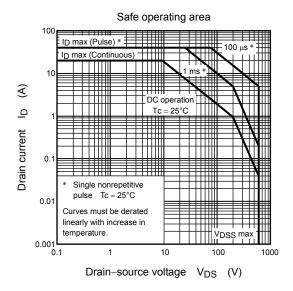


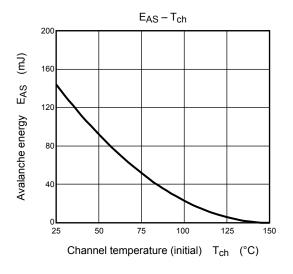


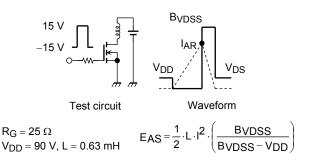












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20070701-EN GENERAL

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